

Kadir Ejderha

List of Publications by Year in descending order

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papers

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citations

687363

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all docs

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docs citations

25
times ranked

459
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis and Comparison of the Main Electrical Characteristics of Cu/n-type Si metal semiconductor structures at wide temperature Range. Silicon, 2022, 14, 3493-3500.	3.3	1
2	Temperature dependence of electrical parameters of the Cu/n-Si metal semiconductor Schottky structures. Journal of Molecular Structure, 2021, 1224, 129057.	3.6	16
3	Temperature dependence of interface-state density distributions in Cu/CuO/n-type Si structures. Materials Today: Proceedings, 2021, 46, 7030-7032.	1.8	0
4	Dependence of Electrical Properties of Ni/n-GaP/Al Schottky Contacts on Measurement Temperature and Thermal Annealing. Journal of Electronic Materials, 2021, 50, 6741-6747.	2.2	9
5	Temperature dependence of interface state density distribution determined from conductanceâ€“frequency measurements in Ni/n-GaP/Al diode. Journal of Materials Science: Materials in Electronics, 2020, 31, 21260-21271.	2.2	7
6	The Effect of Thermal Annealing and Measurement Temperature on Interface State Density Distribution and Time Constant in Ni/n-GaP Rectifying Contacts. Journal of Electronic Materials, 2018, 47, 3502-3509.	2.2	14
7	Characterization of CuO/n-Si heterojunction solar cells produced by thermal evaporation. Materials Science-Poland, 2018, 36, 668-674.	1.0	10
8	THE CHARACTERISTIC DIODE PARAMETERS IN Ti/p-InP CONTACTS PREPARED BY DC SPUTTERING AND EVAPORATION PROCESSES OVER A WIDE MEASUREMENT TEMPERATURE. Surface Review and Letters, 2017, 24, 1750052.	1.1	6
9	Effect of different sound atmospheres on SnO ₂ :Sb thin films prepared by dip coating technique. Modern Physics Letters B, 2017, 31, 1750288.	1.9	1
10	The Characteristic Parameters of Ni/n-6H-SiC Devices Over a Wide Measurement Temperature Range. Silicon, 2017, 9, 395-401.	3.3	19
11	Characteristic diode parameters in thermally annealed Ni/p-InP contacts. Journal of Semiconductors, 2016, 37, 044001.	3.7	7
12	The electrical characterizations and illumination response of Co/N-type GaP junction device. Current Applied Physics, 2015, 15, 1054-1061.	2.4	24
13	Capacitanceâ€“conductanceâ€“currentâ€“voltage characteristics of atomic layer deposited Au/Ti/Al ₂ O ₃ /n-GaAs MIS structures. Materials Science in Semiconductor Processing, 2015, 39, 400-407.	4.0	108
14	The effect of annealing temperature on the electrical characterization of Co/n type GaP Schottky diode. Materials Research Bulletin, 2015, 61, 463-468.	5.2	17
15	Effect of temperature on the current (capacitance and conductance)â€“voltage characteristics of Ti/n-GaAs diode. Journal of Applied Physics, 2014, 116, .	2.5	18
16	Temperature-dependent current-voltage characteristics in thermally annealed ferromagnetic Co/n-GaN Schottky contacts. EPJ Applied Physics, 2014, 68, 20101.	0.7	8
17	Temperature-dependent I-V characteristics in thermally annealed Co/p-InP contacts. EPJ Applied Physics, 2012, 57, 10102.	0.7	6
18	Determination of contact parameters of Ni/n-GaP Schottky contacts. Microelectronics Reliability, 2012, 52, 1005-1011.	1.7	16

#	ARTICLE	IF	CITATIONS
19	Electrical and optical characteristics of Au/PbS/n-6H α C structures prepared by electrodeposition of PbS thin film on n-type 6H α C substrate. Journal of Alloys and Compounds, 2011, 509, 3155-3159.	5.5	14
20	Responses of Pt/n-InP Schottky diode to electron irradiation in different temperature conditions. Journal of Radioanalytical and Nuclear Chemistry, 2011, 289, 145-148.	1.5	10
21	Schottky barrier height modification in Au/n-type 6H α C structures by PbS interfacial layer. Microelectronic Engineering, 2011, 88, 179-182.	2.4	15
22	Dependence of characteristic diode parameters on sample temperature in Ni/epitaxy n-Si contacts. Materials Science in Semiconductor Processing, 2011, 14, 5-12.	4.0	32
23	Influence of interface states on the temperature dependence and current-voltage characteristics of Ni/p-InP Schottky diodes. Superlattices and Microstructures, 2010, 47, 241-252.	3.1	29
24	On temperature-dependent experimental I-V and C-V data of Ni/n-GaN Schottky contacts. Journal of Applied Physics, 2010, 108, .	2.5	104
25	Examination by interfacial layer and inhomogeneous barrier height model of temperature-dependent I-V characteristics in Co/p-InP contacts. Journal of Alloys and Compounds, 2009, 484, 870-876.	5.5	34